L	Hits	Search Text		DB	Time stamp
Number					
2	2	@ad<=20000203 and 'n	' adjl 'electrode'	USPAT;	2004/06/01
		with 'ITO'		US-PGPUB; EPO; JPO;	09:57
				DERWENT;	
				IBM_TDB	
3	6	@ad<=20000203 and 'L	ED'and 'n electrode'	USPAT;	2004/06/01
		with 'ITO'		US-PGPUB; EPO; JPO;	08:15
				DERWENT;	
				IBM_TDB	
4	1		ED' and 'n electrode'	USPAT;	2004/06/01
		with 'ITO'		US-PGPUB; EPO; JPO;	08:13
				DERWENT;	
	_			IBM_TDB	
5	2	@ad<=20000203 and 'n	electrode' with	USPAT;	2004/06/01
		110		US-PGPUB; EPO; JPO;	08:17
				DERWENT;	
	_			IBM_TDB	
6	2	@ad<=20000203 and 'I 'n-electrode'	TO' with	USPAT; US-PGPUB;	2004/06/01 08:17
		11 GIGGELOUG		EPO; JPO;	00.17
				DERWENT;	
7	9	@ad<=20000203 and 't	namana namati audan	IBM_TDB	2004/06/01
'	9	'n-electrode'	ransparent with	USPAT; US-PGPUB;	2004/06/01 08:18
		n creeroue		EPO; JPO;	00.10
				DERWENT;	ç
188	3	@ad<=20000203 and 'g	allium compound! and	IBM_TDB USPAT;	2004/06/01
100	3	'n electrode' and 'p		US-PGPUB;	08:33
1		r control and p		EPO; JPO;	V
				DERWENT;	
189	1207	@ad<=20000203 and (2	57/98) ccls	IBM_TDB USPAT;	2004/06/01
105	1207	ead\-20000203 and (2	377 307 . CC13.	US-PGPUB;	12:23
				EPO; JPO;	
				DERWENT;	
190	661	@ad<=20000203 and (2	57/94).ccls.	IBM_TDB USPAT;	2004/06/01
		(1	.,,,,	US-PGPUB;	08:38
}				EPO; JPO;	
				DERWENT; IBM TDB	
191	444	@ad<=20000203 and (2	57/96).ccls.	USPAT;	2004/06/01
				US-PGPUB;	08:38
				EPO; JPO; DERWENT;	
				IBM TDB	
192 ·	326	@ad<=20000203 and (2	57/97).ccls.	USPAT;	2004/06/01
				US-PGPUB;	08:38
				EPO; JPO; DERWENT;	
				IBM_TDB	
193	936	@ad<=20000203 and (2	57/103).ccls.	USPAT;	2004/06/01
				US-PGPUB; EPO; JPO;	08:39
				DERWENT;	
				IBM_TDB	
194	326	@ad<=20000203 and (2	57/13).ccls.	USPAT;	2004/06/01
				US-PGPUB; EPO; JPO;	08:40
				DERWENT;	
105	005	A-14 00000000 1 15	57/15)	IBM_TDB	0004/05/05
195	235	@ad<=20000203 and (2	5//15).ccls.	USPAT; US-PGPUB;	2004/06/01 08:40
				EPO; JPO;	
				DERWENT;	
				IBM TDB	

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196	341	@ad<=20000203 and (257/22).ccls.	USPAT;	2004/06/01
196	241	ead(-20000203 and (237/22).CC13.	US-PGPUB;	08:40
			EPO; JPO;	
			DERWENT;	
198	3	 @ad<=20000203 and 'n-electrode' same	<pre>IBM_TDB USPAT;</pre>	2004/06/01
198]	'ITO'	US-PGPUB;	10:00
			EPO; JPO;	
			DERWENT;	
200	150	On the Control of the	IBM_TDB	2004/06/01
200	152	<pre>@ad<=20000203 and 'LED' same 'ITO' with 'electrode'</pre>	USPAT; US-PGPUB;	2004/06/01
		electiode	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
202	4	<pre>@ad<=20000203 and 'gallium nitride' same 'ITO' with 'electrode'</pre>	USPAT; US-PGPUB;	2004/06/01
		Tio with electiode	EPO; JPO;	10:02
			DERWENT;	
			IBM_TDB	
203	. 48	@ad<=20000203 and 'LED' with 'ITO' with	USPAT;	2004/06/01
		'electrode'	US-PGPUB; EPO; JPO;	10:16
			DERWENT;	
			IBM_TDB	
204	1		USPAT;	2004/06/01
		with 'ITO' with 'electrode'	US-PGPUB; EPO; JPO;	10:16
			DERWENT;	
			IBM TDB	
205	49	@ad<=20000203 and 'nitride semiconductor'	USPAT;	2004/06/01
		and 'ITO' with 'electrode'	US-PGPUB; EPO; JPO;	10:38
			DERWENT;	
			IBM TDB	
206	47	@ad<=20000203 and 'n' near2 'electrode'	USPAT;	2004/06/01
		with 'ITO'	US-PGPUB;	10:38
			EPO; JPO; DERWENT;	
1			IBM TDB	
207	13	@ad<=20000203 and 'n' near1 'electrode'	USPAT;	2004/06/01
		with 'ITO'	US-PGPUB;	10:38
			EPO; JPO; DERWENT;	
			IBM TDB	,
208	1323	@ad<=20000203 and (257/99).ccls.	USPĀT;	2004/06/01
			US-PGPUB;	12:24
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	507	(257/21).CCLS.	USPAT;	2004/05/30
			US-PGPUB; EPO; JPO;	09:18
			DERWENT;	
			IBM_TDB	
-	16	1 ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	USPĀT;	2002/11/01
		'GaN'	US-PGPUB;	10:53
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	107	=	USPAT;	2004/05/28
		electrode' and 'p-type electrode'	US-PGPUB;	13:32
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	1	@ad<=20000203 and 'GaN' and 'n-type	USPAT;	2004/05/29
		electrode' and 'p-type electrode' with	US-PGPUB;	07:36
		'pad'	EPO; JPO; DERWENT;	
			IBM_TDB_	
		· · · · · · · · · · · · · · · · · · ·	 — — .	

	,		,	
-	2	("6172382").PN.	USPAT;	2002/11/01
			US-PGPUB;	13:44
			EPO; JPO;	
			DERWENT;	
	1	//057/01)	IBM_TDB	
-	16	((257/21).CCLS.) and @ad<=20000203 and	USPAT;	2002/04/22
		'Gan'	US-PGPUB;	16:46
			EPO; JPO;	
			DERWENT;	
	273	6-d<-20000202 and 16-N1 and 1-1-n-n-d-1	IBM_TDB	2002/04/22
-	2/3	@ad<=20000203 and 'GaN' and 'electrode' with 'transparent'	USPAT; US-PGPUB;	2002/04/23
		with transparent	EPO; JPO;	11:26
			DERWENT;	
1			IBM TDB	
_	3	@ad<=20000203 and 'GaN' and 'n-type	USPAT;	2002/04/23
		electrode' and 'p-type electrode' with	US-PGPUB;	09:56
		'transparent'	EPO; JPO;	
	1	oz diib paz cii c	DERWENT;	
			IBM TDB	
_	0	@ad<=20000203 and 'GaN' and 'n-type	USPAT;	2002/04/23
		electrode' with 'trans'	US-PGPUB;	11:01
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	@ad<=20000203 and 'GaN' and 'n-type	USPAT;	2002/04/23
		electrode' with 'transmissive'	US-PGPUB;	11:01
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	7	@ad<=20000203 and 'GaN' and 'transmissive	USPAT;	2002/11/01
		electrode'	US-PGPUB;	16:06
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	996	(257/59).CCLS.	USPAT;	2002/11/01
			US-PGPUB;	10:53
			EPO; JPO;	l
			DERWENT;	
	0	("103 and 'GaN'").PN.	IBM_TDB USPAT;	2002/04/23
-	١	(103 and Gan).PN.	US-PGPUB;	11:14
			EPO; JPO;	1 11.14
			DERWENT;	
			IBM TDB	
_	6	((257/59).CCLS.) and 'GaN'	USPAT;	2002/04/23
			US-PGPUB;	11:23
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	837	(257/72).CCLS.	USPAT;	2002/11/01
			US-PGPUB;	10:53
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	((257/72).CCLS.) and 'GaN' and	USPAT;	2002/04/23
	į	'transparent electrode'	US-PGPUB;	11:24
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/04/22
-	166	@ad<=20000203 and 'GaN' and 'transparent	USPAT;	2002/04/23
		electrode'	US-PGPUB;	11:27
		·	EPO; JPO;	
			DERWENT; IBM TDB	
1_	115	 @ad<=20000203 and 'GaN' and 'n-type	USPAT;	2003/11/06
_	113	electrode' and 'p-type electrode'	US-PGPUB;	15:11
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
		L		

-	16	((257/21).CCLS.) and @ad<=20000203 and	USPAT;	2002/11/01
*	1	'Gan'	US-PGPUB;	10:53
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
-	1128	(257/59).CCLS.	USPĀT;	2002/11/01
			US-PGPUB;	10:54
			EPO; JPO;	
			DERWENT;	
	0.7	(057/70) GGT G	IBM_TDB	2002/11/01
-	957	(257/72).CCLS.	USPAT;	2002/11/01
			US-PGPUB; EPO; JPO;	10:54
			DERWENT;	
			IBM TDB	
_	560	(438/22).CCLS.	USPAT;	2002/11/01
			US-PGPUB;	11:05
			EPO; JPO;	
			DERWENT;	1
			IBM_TDB	
-	1108	((438/22) or (257/79)).CCLS.	USPAT;	2002/11/01
			US-PGPUB;	11:07
			EPO; JPO;	
			DERWENT;	
_	106	 @ad<=20000203 and 'GaN' and 'n-type' and	IBM_TDB USPAT;	2002/11/01
_	100	cad<=20000203 and 'Gan' and 'n-type' and p-type' and ITO'	US-PGPUB;	12:03
		heathe aug tro	EPO; JPO;	12.03
			DERWENT;	
			IBM TDB	i l
_	35	@ad<=20000203 and 'GaN' and 'n-type' same	USPAT;	2002/11/01
		'ITO'	US-PGPUB;	13:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	7979	((257/13-15) or (257/79-103)).CCLS.	USPAT;	2002/11/01
			US-PGPUB;	13:48
			EPO; JPO;	
			DERWENT; IBM TDB	
_	463	(((257/13-15) or (257/79-103)).CCLS.) and	USPAT;	2003/06/04
	103	@ad<=20000203 and 'GaN'	US-PGPUB;	10:03
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	709	(438/22-24).CCLS.	USPAT;	2002/11/01
			US-PGPUB;	13:50
			EPO; JPO;	
			DERWENT;	
1_	0	 @ad<=20000203 and 'light emitting diode'	IBM_TDB USPAT;	2002/11/01
_		and 'n-type electrode' with 'ITO'	US-PGPUB;	15:58
		and if type treetrode wron 110	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	244		USPAT;	2002/11/01
		and 'n-type electrode'	US-PGPUB;	15:47
			EPO; JPO;	
			DERWENT;	
	1	(0-14 0000000 3 12 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	IBM_TDB	2000/11/01
_	13	1 ' -	USPAT;	2002/11/01
		and 'n-type electrode') and ITO	US-PGPUB; EPO; JPO;	15:48
			DERWENT;	
			IBM TDB	
-	0	@ad<=20000203 and 'n-type electrode' with	USPAT;	2002/11/01
		'ITO'	US-PGPUB;	15:58
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

-	0	<pre>@ad<=20000203 and 'n-type electrode' near 'ITO'</pre>	USPAT; US-PGPUB;	2002/11/01 15:59
		110	EPO; JPO;	13.39
			DERWENT;	
			IBM_TDB	
-	55	@ad<=20000203 and 'n-type electrode' and	USPAT;	2002/11/01
		'ITO'	US-PGPUB;	16:03
			EPO; JPO;	
			DERWENT; IBM TDB	
_	1	@ad<=20000203 and 'n-type electrode' and	USPAT;	2002/11/01
	1	'TCO'	US-PGPUB;	16:05
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000 /44 /04
-	49	•	USPAT;	2002/11/01 16:06
		electrode'	US-PGPUB; EPO; JPO;	16:06
			DERWENT;	
			IBM TDB	
_	8	@ad<=20000203 and 'GaN' and 'transmissive	USPĀT;	2002/11/01
		electrode'	US-PGPUB;	16:07
			EPO; JPO;	
			DERWENT;	
_	1197	 @ad<=20000203 and (257/98).ccls.	<pre>IBM_TDB USPAT;</pre>	2004/06/01
-	119/	Gad\-20000203 and \237/30/.0013.	US-PGPUB;	08:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	145	@ad<=20000203 and (257/91).ccls.	USPAT;	2003/06/03
			US-PGPUB;	09:52
			EPO; JPO; DERWENT;	
			IBM TDB	
_	655	@ad<=20000203 and (257/94).ccls.	USPAT;	2003/06/03
			US-PGPUB;	09:53
			EPO; JPO;	
			DERWENT;	
	925	@ad<=20000203 and (257/103).ccls.	IBM_TDB USPAT;	2003/06/03
-	923	eau\-20000203 and \(237/103\).ccis.	US-PGPUB;	09:53
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/05/00
-	1315	@ad<=20000203 and (257/99).ccls.	USPAT; US-PGPUB;	2003/06/03 09:54
			EPO; JPO;	05.53
			DERWENT;	
			IBM_TDB	
-	2	("6100545").PN.	USPĀT;	2003/06/03
			US-PGPUB;	09:54
			EPO; JPO;	
			DERWENT; IBM TDB	
_	7	 @ad<=20000203 and 'GaN' with	USPAT;	2003/06/03
	1	'transparent' and 'n-type electrode' and	US-PGPUB;	13:56
		'p-type electrode'	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/06/02
-	22	<pre>@ad<=20000203 and 'GaN' and 'transparent' and 'n-type electrode' and 'p-type</pre>	USPAT; US-PGPUB;	2003/06/03 13:29
		and 'n-type electrode' and 'p-type	EPO; JPO;	13.27
			DERWENT;	
	1		IBM_TDB	
-	8		USPAT;	2003/06/03
	1	same 'n-type electrode' and 'p-type	US-PGPUB;	13:39
		electrode'	EPO; JPO; DERWENT;	1
	1		IBM TDB	
	l		·	1

-	24	@ad<=20000203 and 'GaN' with 'transparent electrode'	USPAT; US-PGPUB; EPO; JPO;	2003/06/03 13:40
			DERWENT; IBM TDB	
-	16	<pre>@ad<=20000203 and 'Gallium nitride' with 'transparent electrode'</pre>	USPAT; US-PGPUB;	2003/06/03 13:40
		-	EPO; JPO; DERWENT;	
_	26	 @ad<=20000203 and 'GaN' and 'n-type' with	IBM_TDB USPAT;	2003/06/03
		'p-type' same 'transparent electrode'	US-PGPUB; EPO; JPO;	13:57
			DERWENT; IBM TDB	
-	0	transparent electrode' same 'p-type	USPAT; US-PGPUB;	2003/06/03 13:58
		transparent electrode'	EPO; JPO; DERWENT;	
_	0	@ad<=20000203 and 'n-type transparent	IBM_TDB USPAT;	2003/06/03
		electrode' same 'p-type transparent electrode'	US-PGPUB; EPO; JPO;	13:59
	486	(((257/13-15) or (257/79-103)).CCLS.) and	DERWENT; IBM_TDB	2002/11/06
-	400	@ad<=20000203 and 'GaN'	USPAT; US-PGPUB; EPO; JPO;	2003/11/06 15:11
			DERWENT; IBM TDB	
-	314	(((257/13-15) or (257/79-103)).CCLS.) and @ad<=20000203 and 'gallium nitride'	USPAT; US-PGPUB;	2003/06/04 10:04
		garram mrorras	EPO; JPO; DERWENT;	
_	2	"20010042860"	IBM_TDB USPAT;	2003/11/06
			US-PGPUB; EPO; JPO;	13:01
			DERWENT; IBM_TDB	
_	496	(((257/13-15) or (257/79-103)).CCLS.) and @ad<=20000203 and 'GaN'	USPAT; US-PGPUB;	2003/11/06 15:12
			EPO; JPO; DERWENT; IBM TDB	
-	112	<pre>@ad<=20000203 and 'GaN' and 'n-type electrode' same 'p-type electrode'</pre>	USPAT; US-PGPUB;	2003/11/06 15:14
		erections pane p type creations	EPO; JPO; DERWENT;	10.11
_	46	 @ad<=20000203 and 'GaN' and 'n-type	IBM_TDB USPAT;	2003/11/06
		electrode' same 'thickness'	US-PGPUB; EPO; JPO;	15:24
		0-4-20000000 1	DERWENT; IBM_TDB	2002/11/06
-	3	<pre>@ad<=20000203 and 'GaN' and 'thin' with 'n-type electrode'</pre>	USPAT; US-PGPUB; EPO; JPO;	2003/11/06 15:26
			DERWENT; IBM TDB	
-	2	(@ad<=20000203 and 'GaN' and 'thin' with 'n-type electrode') and thickness near3	USPAT; US-PGPUB;	2003/11/06 15:28
		(nm nanometer)	EPO; JPO; DERWENT;	
_	25	•	IBM_TDB USPAT;	2003/11/06
		near3 thickness near3 (nm nanometer)	US-PGPUB; EPO; JPO;	15:39
			DERWENT; IBM TDB	

-	1	@ad<=20000203 and 'GaN' and electrode	USPAT;	2003/11/06
		near3 thickness near3 '30'	US-PGPUB;	15:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	,
-	40	@ad<=20000203 and 'GaN' same 'transparent	USPAT;	2003/11/06
		electrode'	US-PGPUB;	15:35
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	@ad<=20000203 and 'GaN' same	USPAT;	2003/11/06
		'transparent' with 'n type electrode'	US-PGPUB;	15:36
			EPO; JPO;	
	ļ		DERWENT;	
			IBM TDB	
_	116	@ad<=20000203 and 'GaN' and 'n' with	USPAT;	2003/11/06
	110	'electrode' same '50'	US-PGPUB;	15:40
		CICCUIORC DAME OF	EPO; JPO;	10
			DERWENT;	
			IBM TDB	
_	33	@ad<=20000203 and 'GaN' and 'n' near2	USPAT;	2003/11/06
-	33	'electrode' with '50'	US-PGPUB;	15:40
		erectione with 20	EPO; JPO;	15.40
			DERWENT;	
		0 14 00000000 11 10 11 1 1 1 1 1	IBM_TDB	0004/05/00
-	10		USPAT;	2004/05/29
		'electrode' with '50 nm'	US-PGPUB;	07:33
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	19	• • • • • • • • • • • • • • • • • • • •	USPAT;	2003/11/06
		'electrode' with '50 nm'	US-PGPUB;	15:47
	1		EPO; JPO;	
	1		DERWENT;	
	1		IBM_TDB	<u>.</u> .
-	10	@ad<=20000203 and 'GaN' and 'n' adj2	USPAT;	2003/11/06
		'electrode' with '50 nm'	US-PGPUB;	15:48
	}		EPO; JPO;	[
			DERWENT;	1
			IBM_TDB	
-	2	'reflective index' same 'GaN'	USPAT;	2004/03/05
			US-PGPUB;	13:10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	'reflective index of GaN'	USPAT;	2004/03/05
			US-PGPUB;	13:08
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	380	'refractive index' same 'GaN'	USPAT;	2004/05/29
			US-PGPUB;	06:01
			EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
-	0	'refractive index of GaN'	USPAT;	2004/03/05
	1		US-PGPUB;	13:10
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	199	'GaN' with 'refractive index'	USPAT;	2004/03/05
	1 133	Call Will Idliadol vo Index	US-PGPUB;	13:19
			EPO; JPO;]
			DERWENT;	
			IBM TDB	
_	283	@ad<=20000103 and 'sapphire' with	USPAT;	2004/03/05
	203	'refractive index'	US-PGPUB;	13:25
		Tottactive Timey	EPO; JPO;	10.20
			DERWENT;	
			IBM TDB	
	L	<u> </u>	I I DEL I DD	<u> </u>

Γ-	6040	@ad<=20000103 and 'air' with 'refractive	USPAT;	2004/03/05
		index'	US-PGPUB;	13:29
			EPO; JPO;	==
			DERWENT;	
		<u> </u>	IBM_TDB	
-	103	@ad<=20000203 and 'GaN' with 'substrate'	USPAT;	2004/05/28
		and 'n-type electrode' and 'p-type electrode'	US-PGPUB;	15:57
		erections	EPO; JPO; DERWENT;	
			IBM TDB	
_	18	@ad<=20000203 and 'GaN' adj1 'substrate'	USPAT;	2004/05/28
		and 'n-type electrode' and 'p-type	US-PGPUB;	13:54
		electrode'	EPO; JPO;	
			DERWENT;	
		0 14 00000000 1 10 31	IBM_TDB	2004/05/20
_	82	@ad<=20000203 and 'GaN' same 'sapphire' same 'substrate' and 'n-type electrode'	USPAT; US-PGPUB;	2004/05/28 15:57
		and 'p-type electrode'	EPO; JPO;	15.57
		and p type creetrode	DERWENT;	
			IBM TDB	
-	78	@ad<=20000203 and 'substrate' same 'GaN'	USPAT;	2004/05/28
		with 'sapphire' and 'n-type electrode'	US-PGPUB;	16:01
		and 'p-type electrode'	EPO; JPO;	
			DERWENT;	
_	78	 @ad<=20000203 and 'substrate' with 'GaN'	<pre>IBM_TDB USPAT;</pre>	2004/05/29
	'8	with 'sapphire' and 'n-type electrode'	USPAT; US-PGPUB;	06:07
		and 'p-type electrode'	EPO; JPO;	
		F -4F	DERWENT;	
		·	IBM_TDB	
-	854	@ad<=20000203 and 'refractive index' with	USPAT;	2004/05/29
		'GaAs'	US-PGPUB;	06:03
			EPO; JPO; DERWENT;	
	1		IBM TDB	
-	18	@ad<=20000203 and 'GaN substrate' and	USPAT;	2004/06/01
]	'n-type electrode' and 'p-type electrode'	US-PGPUB;	08:32
]		EPO; JPO;	
			DERWENT;	
		0-44 2000000 - 1 1 7 7 1 1 1 1	IBM_TDB	2004/05/20
-	2	,	USPAT; US-PGPUB;	2004/05/29 07:34
		electrode' with 'pad'	EPO; JPO;	07.34
			DERWENT;	
	1		IBM TDB	
-	1	@ad<=20000203 and 'GaN substrate' and	USPAT;	2004/05/29
		'thin' with 'n-type electrode'	US-PGPUB;	07:36
	1		EPO; JPO;	
	1		DERWENT;	
_	12	@ad<=20000203 and 'n-type electrode' and	IBM_TDB USPAT;	2004/05/29
		'p-type electrode' and 'pad electrode'	US-PGPUB;	07:37
	1	2 22	EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
-	0	@ad<=20000203 and 'GaN substrate' and	USPAT;	2004/05/29
	1	'ITO' with 'n-type electrode'	US-PGPUB;	08:23
			EPO; JPO; DERWENT;	
	1		IBM TDB	
-	0	@ad<=20000203 and 'GaN' and 'ITO' with	USPAT;	2004/05/29
		'n-type electrode'	US-PGPUB;	08:23
	1		EPO; JPO;	
ļ	1		DERWENT;	
1_	124	 @ad<=20000203 and 'GaN' and 'ITO' with	IBM_TDB USPAT;	2004/05/29
-	124	'electrode'	US-PGPUB;	08:33
			EPO; JPO;	*****
			DERWENT;	
	<u> </u>		IBM_TDB	

-	0	@ad<=20000203 and 'GaN' and 'ITO' with	USPAT;	2004/05/29
		'n' adj1 'electrode'	US-PGPUB;	08:34
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	61	@ad<=20000203 and 'transparent' same	USPAT;	2004/05/29
	1	'n-type electrode'	US-PGPUB;	08:45
		5/25 52552500	EPO; JPO;	331.13
			DERWENT;	
			IBM TDB	
_	0	@ad<=20000203 and 'n-type electrode' with	USPAT;	2004/05/29
		'ITO'	US-PGPUB;	08:46
		110	EPO; JPO;	00.40
			DERWENT;	
			IBM_TDB	2004/05/20
_	2	1 -	USPAT;	2004/05/29
		'indium tin oxide'	US-PGPUB;	08:46
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	@ad<=20000203 and 'n-type electrode' same	USPAT;	2004/06/01
		'ITO'	US-PGPUB;	08:06
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	"20010042860"	USPĀT;	2004/05/30
			US-PGPUB;	09:21
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	JP10-163531	USPAT;	2004/05/30
			US-PGPUB;	09:22
	1		EPO; JPO;	
			DERWENT;	1
			IBM TDB	
	2	'JP 10163531'	USPAT;	2004/05/30
_	1	UP 10103331	US-PGPUB;	09:24
				09.24
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	2004/05/30
_	83	yamada-motokazu.in.	USPAT;	2004/05/30
	1		US-PGPUB;	09:25
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
-	34	yamada-motokazu.in. and 'LED'	USPAT;	2004/05/30
			US-PGPUB;	09:25
			EPO; JPO;	
			DERWENT;	
			IBM TDB	